

MOS FIELD EFFECT TRANSISTOR

2SK1398

N-CHANNEL MOS FET FOR HIGH SPEED SWITCHING

* DESCRIPTION

The 2SK1398 is N-channel MOS Field Effect Transistor designed for a high-speed switching device in digital circuits. The 2SK1398 is driven by a 2.5-V power source, it is suitable for applications including headphone stereos which need power saving.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK1398	SST

FEATURES

- Directly driven by ICs having a 3-V power supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Can be used complementary with the 2SJ184.

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

 Not necessary to consider driving current 	because of	its high input imped	dance.					
 Possible to reduce the number of parts by omitting the bias resistor. 								
Can be used complementary with the 2SJ184.								
	3.1	S. Ch						
ABSOLUTE MAXIMUM RATINGS (TA = 25° C)								
Drain to Source Voltage (Vgs= 0 V)	Vdss	50	V					
Gate to Source Voltage (VDs= 0 V)	Vgss	±7.0	V					
Drain Current (DC)	ID(DC)	±100	mA					
Drain Current (pulse) Note	D(pulse)	±200	mA					
Total Power Dissipation	Рт	250	mW					
Channel Temperature	Tch	150	°C					
Storage Temperature	Tstg	–55 to +150	°C					

Note PW \leq 10 ms, Duty cycle \leq 50 %

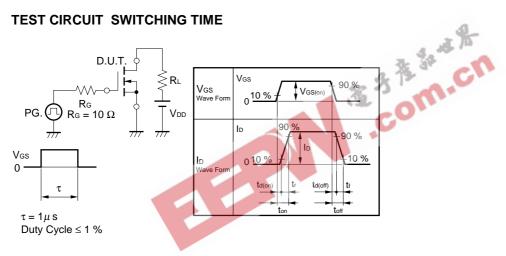
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ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

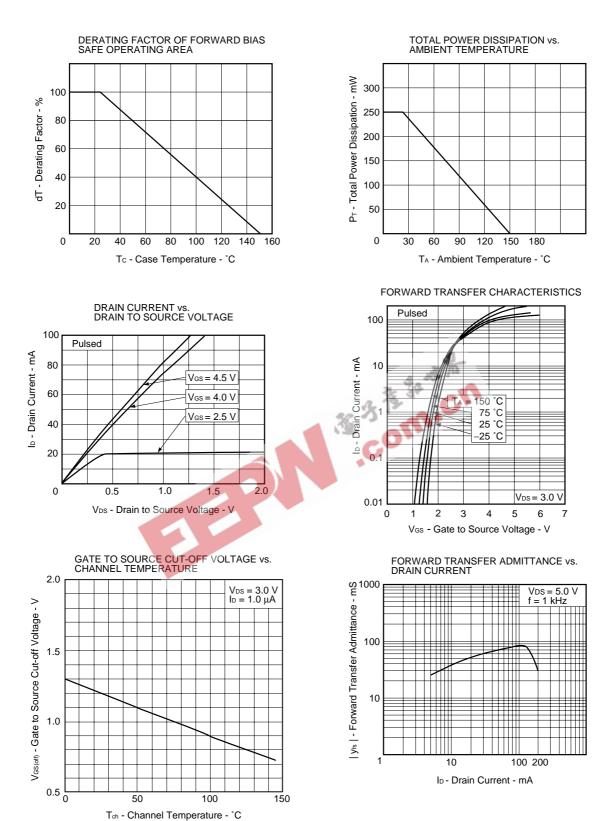
NEC

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	Vds = 50 V, Vgs = 0 V			10	μA
Gate Leakage Current	lgss	$V_{GS} = \pm 7.0 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			±5.0	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	$V_{DS} = 3.0 \text{ V}, \text{ Id} = 1.0 \ \mu\text{A}$	0.9	1.2	1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = 3.0 V, I _D = 10 mA	20	38		mS
Drain to Source On-state Resistance	RDS(on)1	V _{GS} = 2.5 V, I _D = 10 mA		22	40	Ω
	RDS(on)2	V _{GS} = 4.0 V, I _D = 10 mA		14	20	Ω
Input Capacitance	Ciss	VDS = 3.0 V		8		pF
Output Capacitance	Coss	V _{GS} = 0 V		7		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		3		pF
Turn-on Delay Time	td(on)	V _{DD} = 3.0 V		15		ns
Rise Time	tr	I _D = 20 mA		100		ns
Turn-off Delay Time	td(off)	V _{GS(on)} = 3.0 V		30		ns
Fall Time	tr	R _G = 10 Ω, R∟ = 150 Ω		35		ns

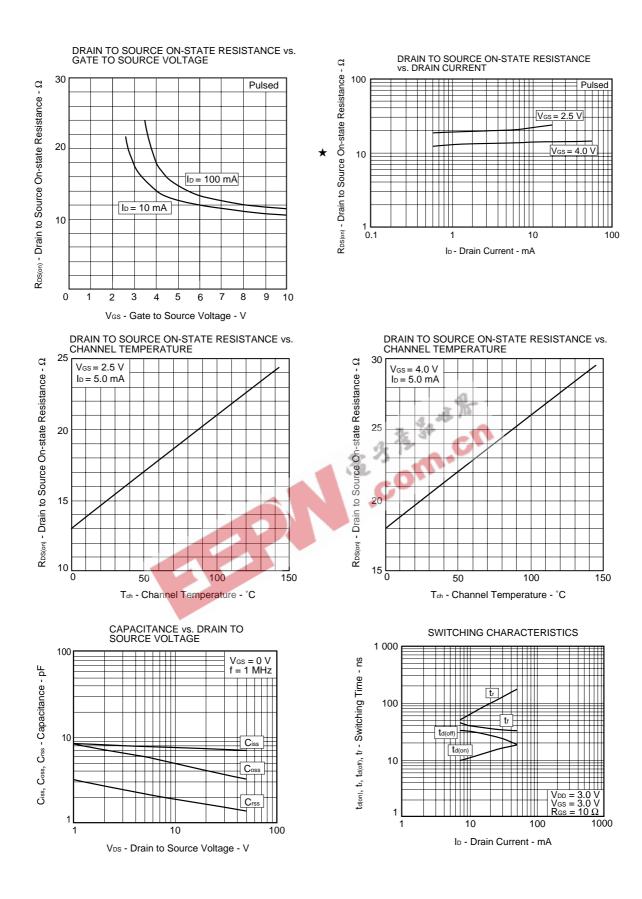
TEST CIRCUIT SWITCHING TIME



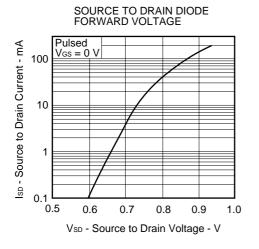
TYPICAL CHARACTERISTICS (TA = 25 °C)



Data Sheet D14772EJ2V0DS00



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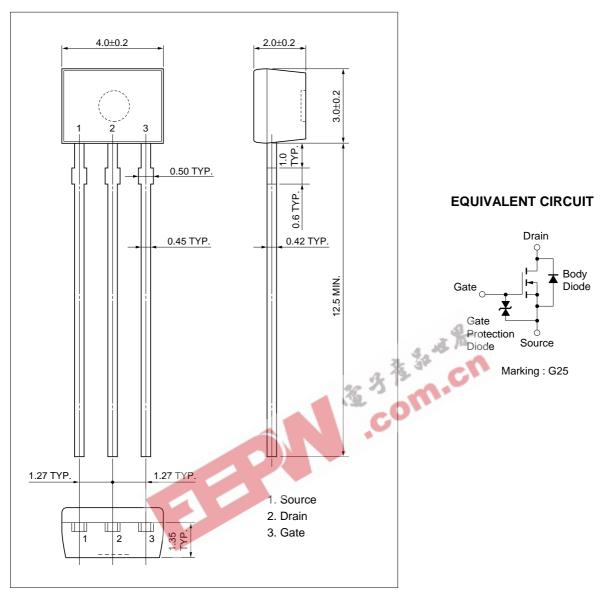




Data Sheet D14772EJ2V0DS00

PACKAGE DRAWING (Unit: mm)

SST



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device. [MEMO]



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